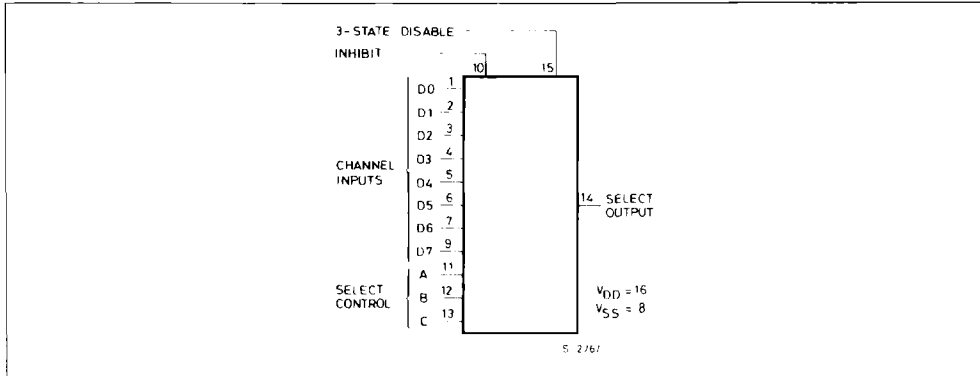


FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{s:g}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

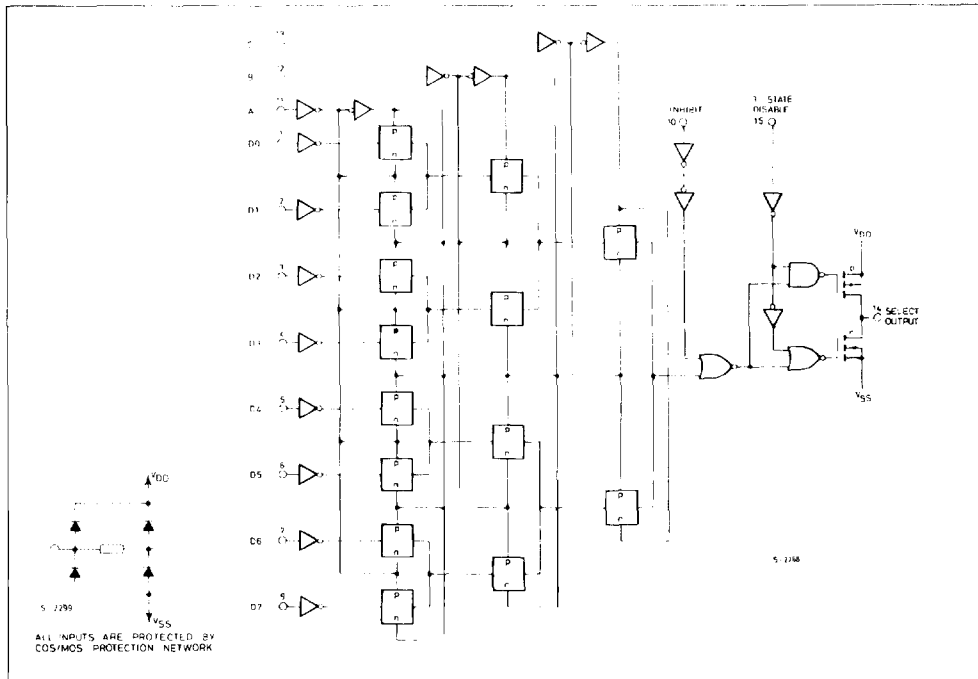
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to + 18	V
	HCF Types	3 to + 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

TRUTH TABLE

Sel. Cont.			Inh.	3-State Disable	Sel. Output
A	B	C			
0	0	0	0	0	D0
1	0	0	0	0	D1
0	1	0	0	0	D2
1	1	0	0	0	D3
0	0	1	0	0	D4
1	0	1	0	0	D5
0	1	1	0	0	D6
1	1	1	0	0	D7
X	X	X	1	0	0
X	X	X	X	1	High Z

1 = High Level 0 = Low Level X = Dont Care

LOGIC DIAGRAMS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

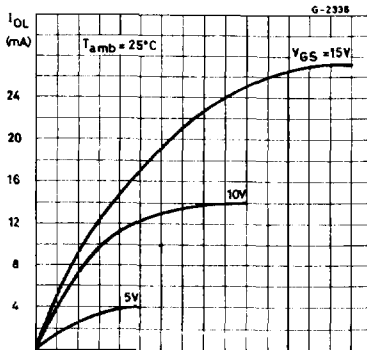
Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150
			0/10			10		10		0.04	10		300
			0/15			15		20		0.04	20		600
		HCF Types	0/20			20		100		0.08	100		3000
			0/5			5		20		0.04	20		150
			0/10			10		40		0.04	40		300
		0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		
		0/10		< 1	10	9.95		9.95			9.95		
		0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	
		10/0		< 1	10		0.05			0.05		0.05	
		15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		
			1/9	< 1	10	7		7			7		
			1.5/13.5	< 1	15	11		11			11		
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	
			9/1	< 1	10		3			3		3	
			13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36	
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9	
		HCF Types	0/15	13.5		15	-4.2		-3.4	-6.8		-2.4	
			0/5	2.5		5	-1.53		-1.36	-3.2		-1.1	
			0/5	4.6		5	-0.52		-0.44	-1		-0.36	
		0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
		0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1
I _{O max}	3-State Output Leakage Current	HCC Types	0/18	0/18		18		± 0.4		$\pm 10^{-4}$	± 0.4		± 12
		HCF Types	0/18	0/18		18		± 1.0		$\pm 10^{-4}$	± 1.0		7.5
C _I	Input Capacitance			Any Input						5	7.5		pF

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

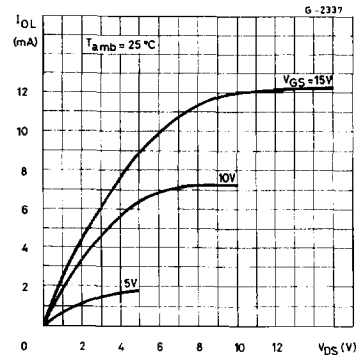
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$,
typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions	Value			Unit	
			V_{DD} (V)	Min.	Typ.		Max.
t_{PHL} , t_{PLH}	Propagation Delay Time Inhibit to Output		5		140	280	ns
			10		70	140	
			15		50	100	
t_{PHL} , t_{PLH}	Propagation Delay Time "A" Select to Output		5		200	400	ns
			10		85	170	
			15		60	120	
t_{PHL} , t_{PLH}	Propagation Delay Time Data to Output		5		180	360	ns
			10		75	150	
			15		55	110	
t_{PZL} , t_{PLZ} t_{PHZ} , t_{PZH}	3-state Disable Delay Time		5		60	120	ns
			10		30	60	
			15		20	40	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

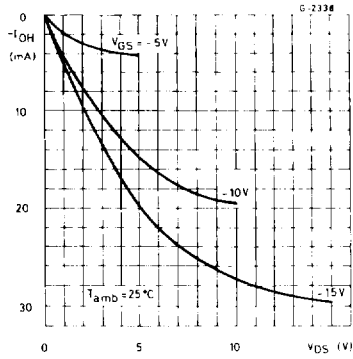
Typical Output Low (sink) Current Characteristics.



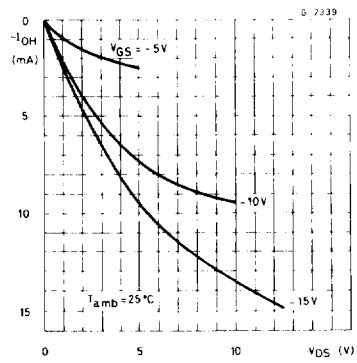
Minimum Output Low (sink) Current Characteristics.



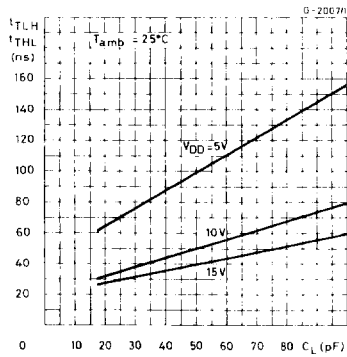
Typical Output High (source) Current Characteristics.



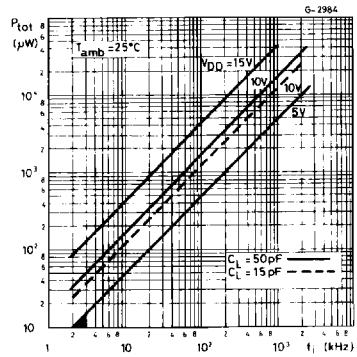
Minimum Output High (source) Current Characteristics.



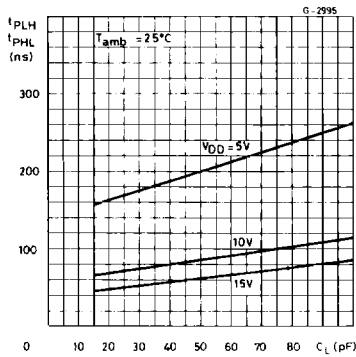
Typical Transition Time vs. Load Capacitance.



Typical Dynamic Power Dissipation vs. Input Frequency.

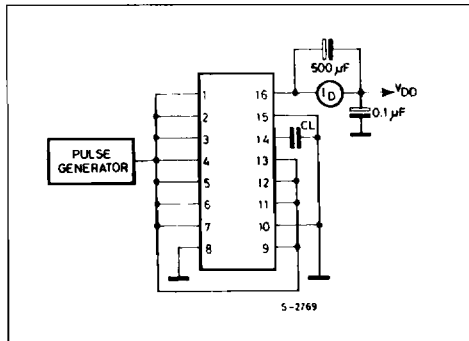


Typical Propagation Delay Time as a Function of Load Capacitance ("A" select to output).

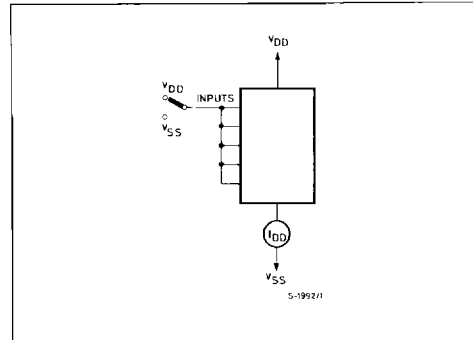


TEST CIRCUITS

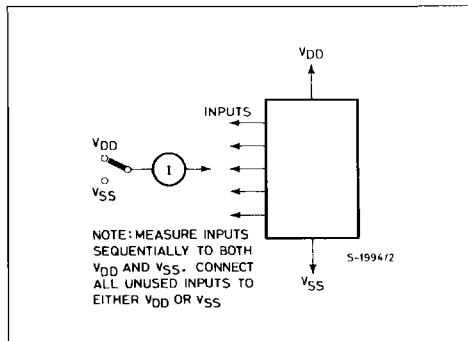
Dynamic Power Dissipation Test Circuit.



Quiescent Device Current Test Circuit.



Input Current Test Circuit.



Input Voltage Test Circuit.

